

**Radiation Hardened Power-Up/Down
Microprocessor Reset Circuit**



The Radiation Hardened IS-705RH is a monolithic device that monitors the power supply voltage used by satellite control units and provides a

reset output pulse during power-up and power-down. The reset threshold is 4.65V (Typ) and the reset pulse width is set at 200ms (Typ). A watchdog circuit is incorporated for easy interfacing with microprocessors and controllers. If the watchdog input has not been toggled within a preset 1.6s (Typ) time period, an output signal is generated, which can be used as an interrupt. The power function input (PFI) may be used to monitor other voltage levels. The circuit has a 1.25V (Typ) threshold and provides a PFO output when low voltage is detected. An active-low manual reset input in also provided for direct control of the reset function.

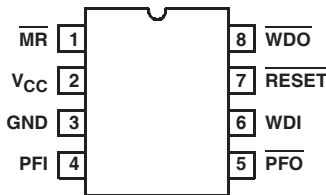
Constructed with the Intersil UHF2X-CMOS process, these devices have been specifically designed to provide highly reliable performance in harsh radiation environments. This process has been tested for single event latch-up and has demonstrated an immunity to 90MeV/mg/cm².

Specifications for Rad Hard QML devices are controlled by the Defense Supply Center in Columbus (DSCC). The SMD numbers listed here must be used when ordering.

Detailed Electrical Specifications for these devices are contained in SMD 5962-00538. A “hot-link” is provided on our homepage for downloading.

Pinout

**IS9-705RH
FLATPACK
TOP VIEW**



Features

- Electrically Screened to SMD # 5962-00538
- QML Qualified per MIL-PRF-38535 Requirements
- Radiation Hardness
 - Total Dose 100 krad(Si) (Max)
 - Single Event Latch-up >90MeV/mg/cm²
- Precision 4.65V Voltage Monitor
- Wide Operating Supply Range 1.2V to 5.5V
- Low Supply Current 420µA (Typ)
- 200ms (Typ) $\overline{\text{RESET}}$ Pulse Width

Applications

- Flight Computers
- Controllers
- Critical Microprocessor Power Monitoring
- Reliable Replacement of Discrete Solutions

Ordering Information

ORDERING NUMBER	INTERNAL MKT. NUMBER	TEMP. RANGE (°C)
5962R0053801QXC	IS9-705RH-8	-55 to 125
5962R0053801VXC	IS9-705RH-Q	-55 to 125
5962R0053801V9A	IS0-705RH-Q	-55 to 125
IS9-705RH/Proto	IS9-705RH/Proto	-55 to 125

Die Characteristics

DIE DIMENSIONS:

1500µm x 1830µm (59 mils x 72 mils)
 Thickness: 483µm ±25.4µm (19 mils ±1 mil)

INTERFACE MATERIALS

Glassivation

Type: Nitride (Si₃N₄) over Silox (SiO₂)
 Nitride Thickness: 4.0kÅ ±1.0kÅ
 Silox Thickness: 12.0kÅ ±4.0kÅ

Top Metallization

Top Metal 3: TiAlCu
 Thickness: 0.8µm ±0.02µm
 Metal 1 and 2: TiAlCu
 Thickness: 0.4µm ±0.01µm

Metallization Mask Layout

Substrate:

UHF2X-CMOS

Backside Finish:

Silicon

ASSEMBLY RELATED INFORMATION

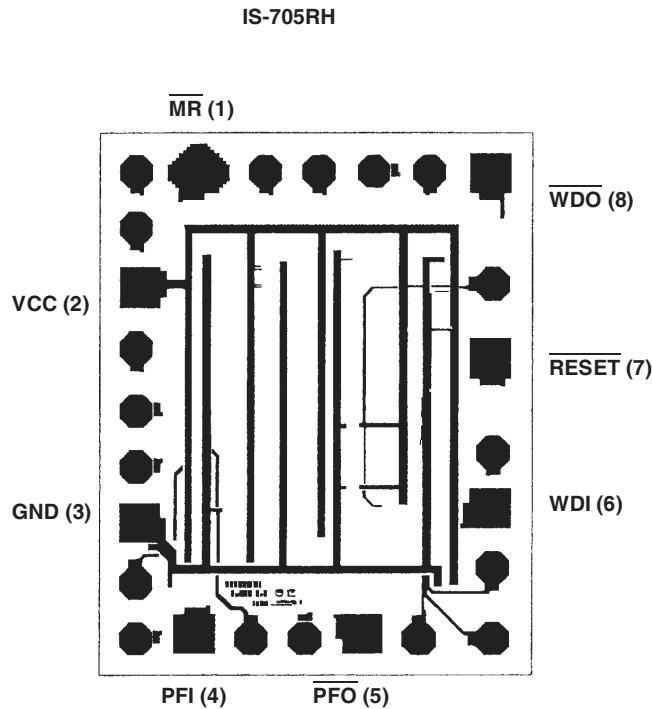
Substrate Potential:

Backside internally connected to GND
 (May be left floating or connected to GND.)

ADDITIONAL INFORMATION

Worst Case Current Density:

<2.0 x 10⁵ A/cm²



NOTES:

- 1. Octagonal trim pads should be left unconnected.

All Intersil U.S. products are manufactured, assembled and tested utilizing ISO9000 quality systems.
 Intersil Corporation's quality certifications can be viewed at www.intersil.com/design/quality

Intersil products are sold by description only. Intersil Corporation reserves the right to make changes in circuit design, software and/or specifications at any time without notice. Accordingly, the reader is cautioned to verify that data sheets are current before placing orders. Information furnished by Intersil is believed to be accurate and reliable. However, no responsibility is assumed by Intersil or its subsidiaries for its use; nor for any infringements of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of Intersil or its subsidiaries.

For information regarding Intersil Corporation and its products, see www.intersil.com